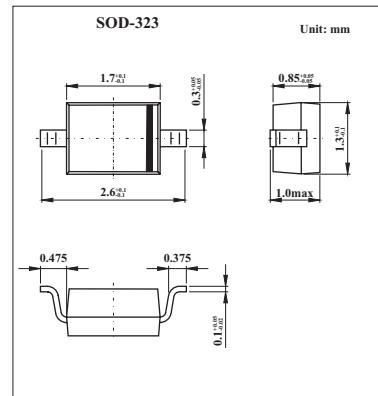


Silicon Epitaxial Planar Diode**1SV245****■ Features**

- High Capacitance Ratio:C_{2V}/C_{25V} = 5.7(Typ.)
- Low Series Resistance:r_s = 1.2 Ω (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.

**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Peak Reverse Voltage	V _{RM}	35(R _L = 10 KΩ)	V
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V _R	I _R = 1 μ A	30			V
Reverse Current	I _R	V _R = 28 V			10	nA
Capacitance	C _{2V}	f = 1 MHz; V _R = 2 V	3.31		4.55	pF
	C _{25V}	f = 1 MHz; V _R = 25 V	0.61		0.77	
Capacitance Ratio	C _{2V} /C _{25V}		5	5.7	6.5	
Series Resistance	r _s	V _R = 1V, f = 470 MHz		1.2	2.0	Ω

Note :

Units are compounded in one package and are mathed to 6.0%

$$\frac{C(\text{Max.}) - C(\text{Min.})}{C(\text{Min.})} \leq 0.06$$

(V_R=2~25V)

■ Marking

Marking	T3
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